

AN: PAT 1997-463782

TI: Organic metal wafer growth of aluminium gallium arsenide  
**thin film** for laser diode involves adding indium on crystalline  
face after interrupting the growth of aluminium-gallium-arsenic  
barrier layer

PN: JP09214052-A

PD: 15.08.1997

AB: The growth involves growing **thin film** crystal containing  
one layer or multilayer AlGaAs barrier layer (3) on GaAs  
substrate (1). Thus, epitaxial crystal for laser diode is  
produced. In the middle of growth of AlGaAs barrier layer, the  
growth is interrupted and In is added on crystalline front face.  
; Improved light emitting life of laser. Reduced crystal defect  
generation.

PA: (HITD ) HITACHI CABLE LTD;

FA: JP09214052-A 15.08.1997;

CO: JP;

IC: C23C-016/48; H01L-021/205; H01S-003/18;

MC: L04-A02A; L04-A02D; L04-E03B; U11-C01B; U11-C01J3A;

DC: L03; U11;

FN: 1997463782.gif

PR: JP0016252 01.02.1996;

FP: 15.08.1997

UP: 20.10.1997

